

1. General description

Planar passivated high commutation three quadrant triac in a TO252 (DPAK) surface-mountable plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- High commutation capability with sensitive gate
- · Planar passivated for voltage ruggedness and reliability
- · Sensitive gate for easy logic level triggering
- Surface-mountable package
- Triggering in three quadrants only

3. Applications

- AC solenoids
- General purpose motor control
- Home appliances

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	-	4	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	-	25	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ t _p = 16.7 ms	-	-	-	27	A
Tj	junction temperature			-	-	125	°C
Static chara	acteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	-	-	10	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	12	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
Dynamic cl	haracteristics	·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	30	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 4 A; dV _{com} /dt = 10 V/µs; gate open circuit	2.1	-	-	A/ms
		V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 4 A; dV _{com} /dt = 0.1 V/µs; gate open circuit	8	-	-	A/ms

5. Pinning information

Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		T2
2	T2	main terminal 2		sym051
3	G	gate		Symoor
mb	T2	mounting base; main terminal 2		
			DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA204S-800E	TO252	BTA204S-800E,118	Reel	2500	TO252N	4-Nov-2016

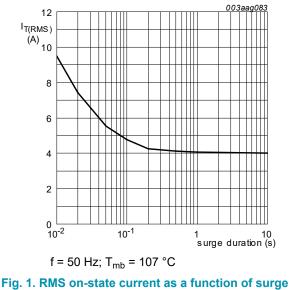


7. Limiting values

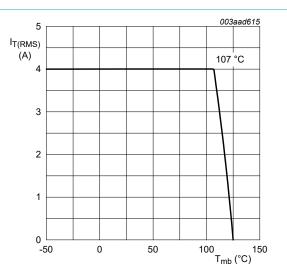
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	4	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	25	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	27	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	3.1	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

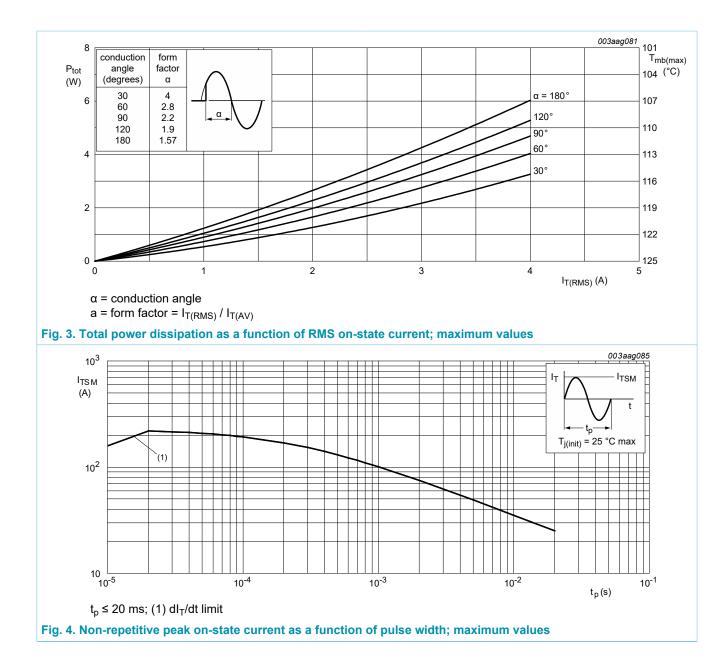


duration; maximum values



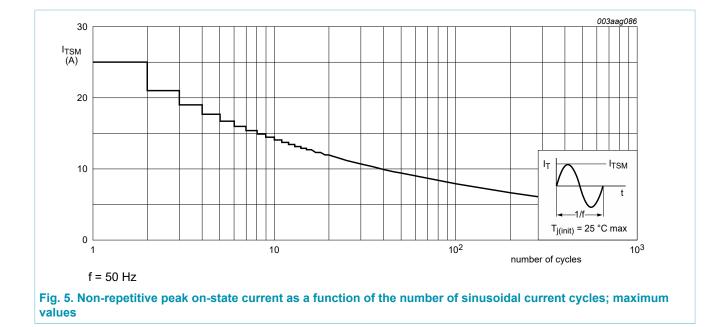


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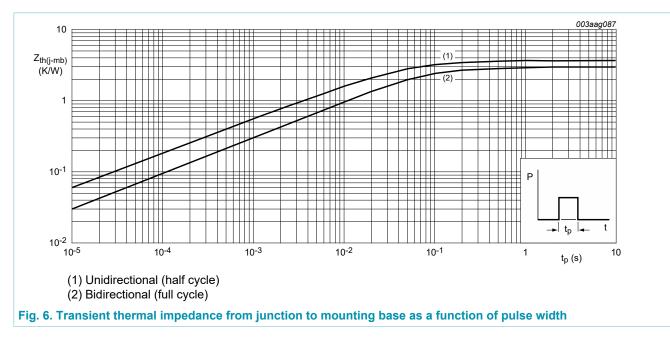




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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; <u>Fig. 6</u>	-	-	3	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	3.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air; printed circuit board (FR4) mounted	-	75	-	K/W



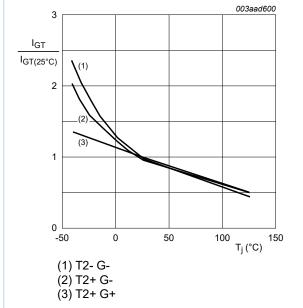
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9. Characteristics

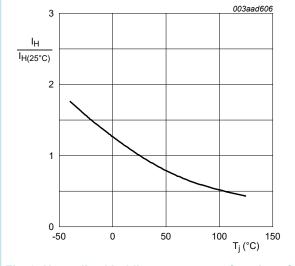
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · ·			,
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	-	10	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	12	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	18	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	12	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	12	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 11</u>	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; <u>Fig. 11</u>	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	30	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T _j = 125 °C; I _{T(RMS)} = 4 A; dV _{com} /dt = 10 V/µs; gate open circuit	2.1	-	-	A/ms
		$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 0.1 \text{ V}/\mu\text{s}; \text{ gate open circuit}$	8	-	-	A/ms

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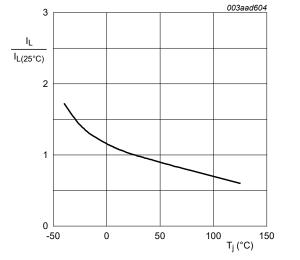
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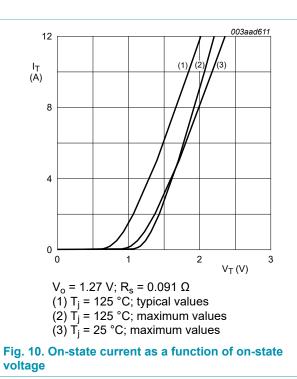






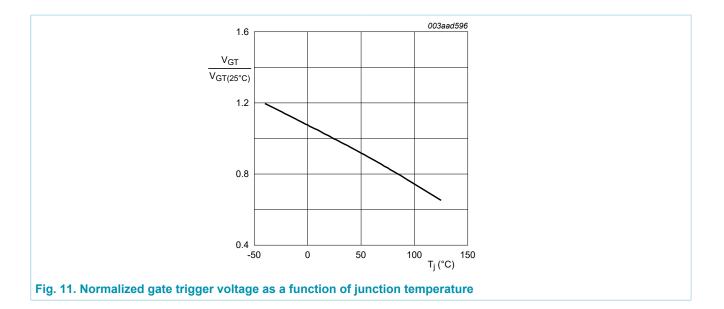






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10. Package outline

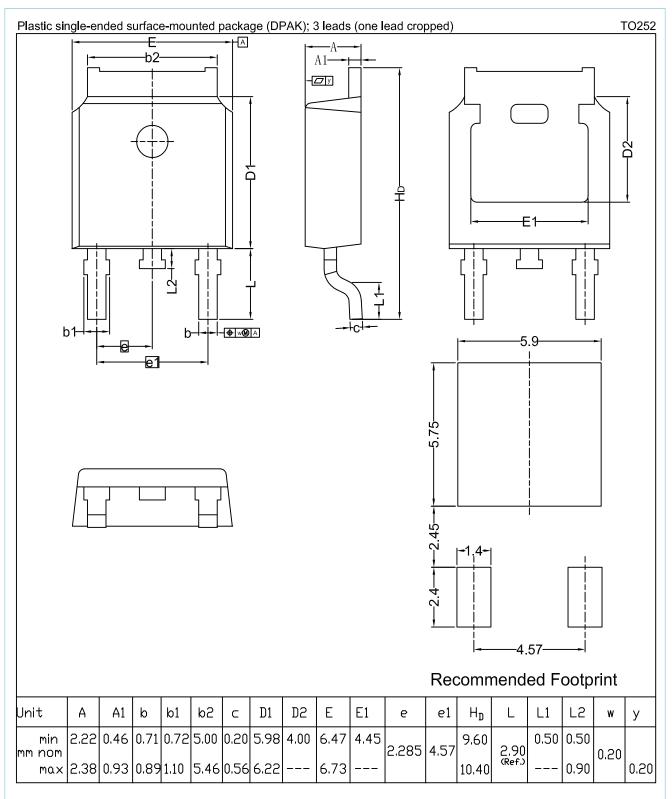


Fig. 12. Package outline DPAK (SOT428)

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11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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